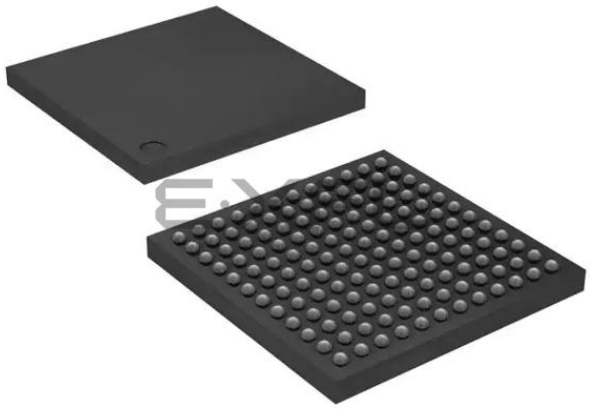

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Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, SD, SPI, UART/USART, USB, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM, WDT
Number of I/O	95
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 53x16b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LBGA
Supplier Device Package	144-MAPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk61fn1m0vmd12

Table 4. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{IND}	Input leakage current, digital pins					2, 3
	• $V_{SS} \le V_{IN} \le V_{IL}$					
	• All digital pins	—	0.002	0.5	µA	
	• $V_{IN} = V_{DD}$					
	• All digital pins except PTD7	—	0.002	0.5	µA	
	• PTD7	—	0.004	1	µA	
I_{IND}	Input leakage current, digital pins					2, 3, 4
	• $V_{IL} < V_{IN} < V_{DD}$					
	• V_{DD} = 3.6 V	—	18	26	µA	
	• V_{DD} = 3.0 V	—	12	19	µA	
	• V_{DD} = 2.5 V	—	8	13	µA	
	• V_{DD} = 1.7 V	—	3	6	µA	
I_{IND}	Input leakage current, digital pins					2, 3
	• $V_{DD} < V_{IN} < 5.5$ V	—	1	50	µA	
Z_{IND}	Input impedance examples, digital pins					2, 5
	• V_{DD} = 3.6 V	—	—	48	kΩ	
	• V_{DD} = 3.0 V	—	—	55	kΩ	
	• V_{DD} = 2.5 V	—	—	57	kΩ	
	• V_{DD} = 1.7 V	—	—	85	kΩ	
I_{IN_Tamper}	Input leakage current (per Tamper pin) for full temperature range	—	—	1	µA	
I_{IN_Tamper}	Input leakage current (per Tamper pin) at 25°C	—	—	0.025	µA	
R_{PU}	Internal pullup resistors (except Tamper pins)	20	—	50	kΩ	6
R_{PD}	Internal pulldown resistors (except Tamper pins)	20	—	50	kΩ	7

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.
2. Digital pins have an associated GPIO port function and have 5V tolerant inputs, except EXTAL and XTAL.
3. Internal pull-up/pull-down resistors disabled.
4. Characterized, not tested in production.
5. Examples calculated using V_{IL} relation, V_{DD}, and max I_{IND}: $Z_{IND}=V_{IL}/I_{IND}$. This is the impedance needed to pull a high signal to a level below V_{IL} due to leakage when $V_{IL} < V_{IN} < V_{DD}$. These examples assume signal source low = 0 V. See Figure 2.
6. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}
7. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{DD}

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash					2
	• @ 1.8V	—	49.28	73.85	mA	
	• @ 3.0V	—	49.08	73.93	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					3
	• @ 1.8V	—	74.43	99.97	mA	
	• @ 3.0V	—	74.28	100.41	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	34.67	58.5	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	18.03	41.91	mA	4
I_{DD_STOP}	Stop mode current at 3.0 V					
	• @ –40 to 25°C	—	1.25	1.62	mA	
	• @ 70°C	—	2.93	4.39	mA	
	• @ 105°C	—	7.08	10.74	mA	
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	—	1.03	4.48	mA	5
I_{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	—	1.58	4.96	mA	5
I_{DD_VLPW}	Very-low-power wait mode current at 3.0 V	—	0.64	4.29	mA	5
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	• @ –40 to 25°C	—	0.22	0.38	mA	
	• @ 70°C	—	0.78	1.33	mA	
	• @ 105°C	—	2.18	3.56	mA	
I_{DD_LLS}	Low leakage stop mode current at 3.0 V					
	• @ –40 to 25°C	—	0.22	0.37	mA	
	• @ 70°C	—	0.78	1.33	mA	
	• @ 105°C	—	2.16	3.52	mA	
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					
	• @ –40 to 25°C	—	4.09	5.58	µA	
	• @ 70°C	—	20.98	28.93	µA	
	• @ 105°C	—	84.95	111.15	µA	
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V					

Table continues on the next page...

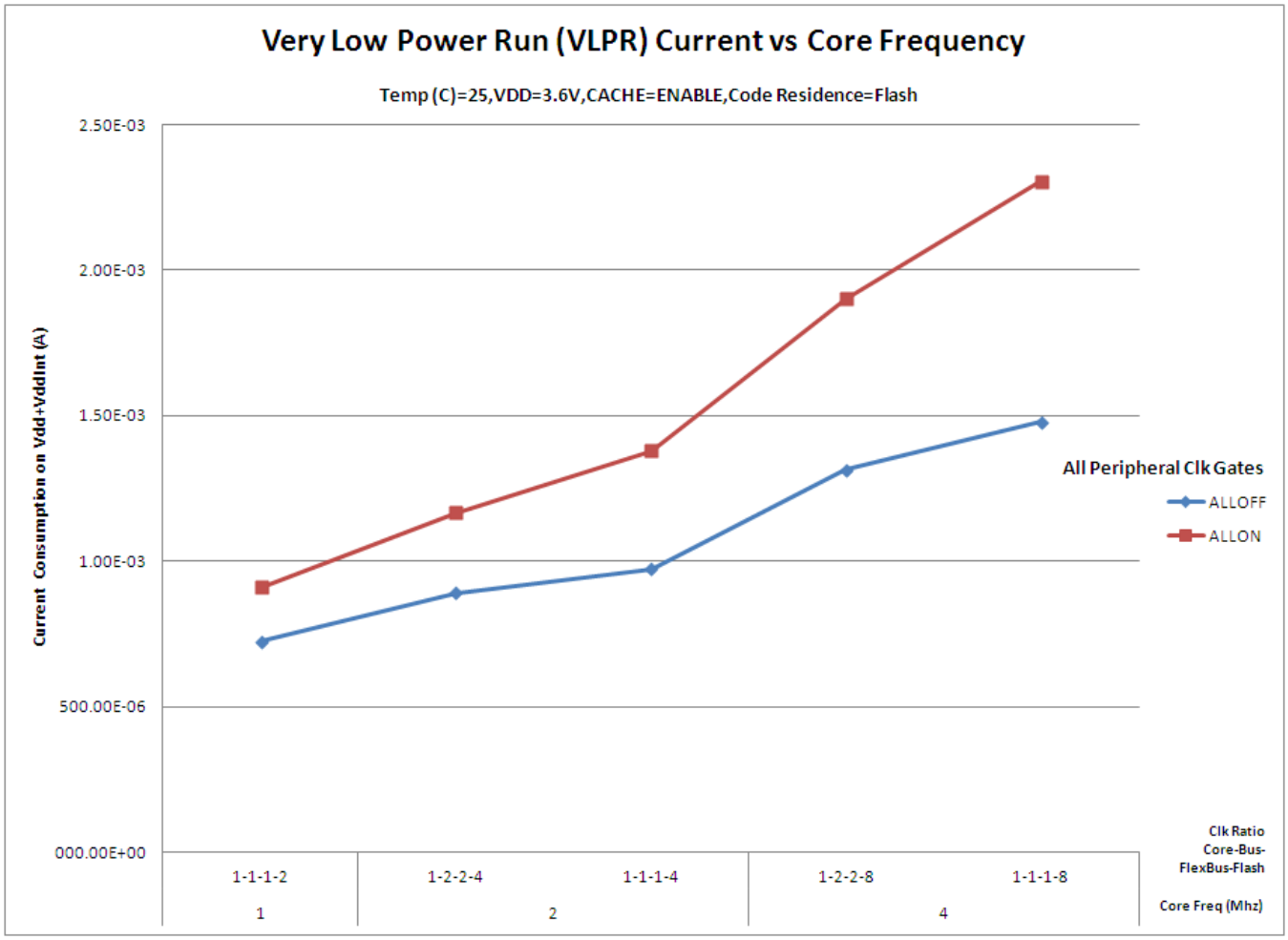

Figure 4. VLPR mode supply current vs. core frequency

5.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 256MAPBGA

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V_{RE1}	Radiated emissions voltage, band 1	0.15–50	21	dBµV	1, 2, 3
V_{RE2}	Radiated emissions voltage, band 2	50–150	24	dBµV	
V_{RE3}	Radiated emissions voltage, band 3	150–500	29	dBµV	
V_{RE4}	Radiated emissions voltage, band 4	500–1000	28	dBµV	

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. V_{DD} = 3.3 V, T_A = 25 °C, f_{OSC} = 12 MHz (crystal), f_{SYS} = 72 MHz, f_{BUS} = 72 MHz
3. Determined according to IEC Standard JESD78, *IC Latch-Up Test*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for "EMC design."

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF
$C_{IN\_D\_io60}$	Input capacitance: fast digital pins	—	9	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	120	MHz	
f_{SYS_USBFS}	System and core clock when Full Speed USB in operation	20	—	MHz	
f_{SYS_USBHS}	System and core clock when High Speed USB in operation	60	—	MHz	
f_{ENET}	System and core clock when ethernet in operation • 10 Mbps • 100 Mbps	 5 50	 — —	MHz	
f_{BUS}	Bus clock	—	60	MHz	
FB_CLK	FlexBus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode[1]					
f_{SYS}	System and core clock	—	4	MHz	

Table continues on the next page...

Table 10. General switching specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
t_{io50}	Port rise and fall time (high drive strength)				6
	• Slew disabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	7	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	3	ns	—
	• Slew enabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	28	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	14	ns	—
t_{io50}	Port rise and fall time (low drive strength)				7
	• Slew disabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	18	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	9	ns	—
	• Slew enabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	48	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	24	ns	—
t_{io60}	Port rise and fall time (high drive strength)				6
	• Slew disabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	6	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	3	ns	—
	• Slew enabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	28	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	14	ns	—
t_{io60}	Port rise and fall time (low drive strength)				7
	• Slew disabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	18	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	6	ns	—
	• Slew enabled				
	• 1.71 ≤ V_{DD} ≤ 2.7V	—	48	ns	—
	• 2.7 ≤ V_{DD} ≤ 3.6V	—	24	ns	—

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.
3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
4. 75 pF load
5. 15 pF load
6. 25 pF load
7. 15 pF load

NOTES:

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)* with the single layer board horizontal. Board meets JESD51-9 specification.
3. Determined according to JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)* with the board horizontal.
4. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*. Board temperature is measured on the top surface of the board near the package.
5. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
6. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 Debug trace timing specifications

Table 12. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
T_{cyc}	Clock period	Frequency dependent		MHz
T_{wl}	Low pulse width	2	—	ns
T_{wh}	High pulse width	2	—	ns
T_r	Clock and data rise time	—	3	ns
T_f	Clock and data fall time	—	3	ns
T_s	Data setup	3	—	ns
T_h	Data hold	2	—	ns

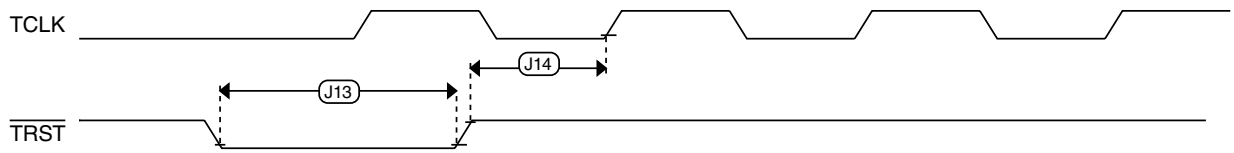

Figure 10. $\overline{\text{TRST}}$ timing

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

6.3.1 MCG specifications

Table 15. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal VDD and 25 °C	—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	—	± 0.3	± 0.6	$\%f_{dco}$	1
$\Delta f_{dco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM only	—	± 0.2	± 0.5	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C	—	± 4.5	—	$\%f_{dco}$	1
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C	—	4	—	MHz	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C	3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00	(3/5) x f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11	(16/5) x f_{ints_t}	—	—	kHz	
FLL						
f_{fll_ref}	FLL reference frequency range	31.25	—	39.0625	kHz	

Table continues on the next page...

Table 21. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk128k}$ $t_{rd1blk256k}$	• 128 KB data flash • 256 KB program flash 256 KB data flash	— —	— —	0.5 1.0	ms ms	
$t_{rd1sec4k}$	Read 1s Section execution time (4 KB flash)	—	—	100	µs	1
t_{pgmchk}	Program Check execution time	—	—	80	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	40	µs	1
t_{pgm8}	Program Phrase execution time	—	70	150	µs	
$t_{ersblk128k}$ $t_{ersblk256k}$	Erase Flash Block execution time • 128 KB data flash • 256 KB program flash 256 KB data flash	— —	110 220	925 1850	ms ms	2
t_{ersscr}	Erase Flash Sector execution time	—	15	115	ms	2
$t_{pgmsec4k}$	Program Section execution time (4KB flash)	—	20	—	ms	
$t_{rd1allx}$ $t_{rd1alln}$	Read 1s All Blocks execution time • FlexNVM devices • Program flash only devices	— —	— —	3.4 3.4	ms ms	
t_{rdonce}	Read Once execution time	—	—	30	µs	1
$t_{pgmonce}$	Program Once execution time	—	70	—	µs	
t_{ersall}	Erase All Blocks execution time	—	650	5600	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1
$t_{swapx01}$ $t_{swapx02}$ $t_{swapx04}$ $t_{swapx08}$	Swap Control execution time • control code 0x01 • control code 0x02 • control code 0x04 • control code 0x08	— — — —	200 70 70 —	— 150 150 30	µs µs µs µs	
$t_{pgmpart64k}$ $t_{pgmpart256k}$	Program Partition for EEPROM execution time • 64 KB EEPROM backup • 256 KB EEPROM backup	— —	235 240	— —	ms ms	
$t_{setramff}$ $t_{setram64k}$ $t_{setram128k}$ $t_{setram256k}$	Set FlexRAM Function execution time: • Control Code 0xFF • 64 KB EEPROM backup • 128 KB EEPROM backup • 256 KB EEPROM backup	— — — —	205 1.6 2.7 4.8	— 2.5 3.8 6.2	µs ms ms ms	
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	140	225	µs	3
$t_{eewr8b64k}$	Byte-write to FlexRAM execution time:	—	400	1700	µs	

Table continues on the next page...

6.4.2 EzPort switching specifications

Table 24. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{SYS}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{SYS}/8$	MHz
EP2	$\overline{\text{EZP\_CS}}$ negation to next $\overline{\text{EZP\_CS}}$ assertion	2 x t_{EZP_CK}	—	ns
EP3	$\overline{\text{EZP\_CS}}$ input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{\text{EZP\_CS}}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	16	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{\text{EZP\_CS}}$ negation to EZP_Q tri-state	—	12	ns

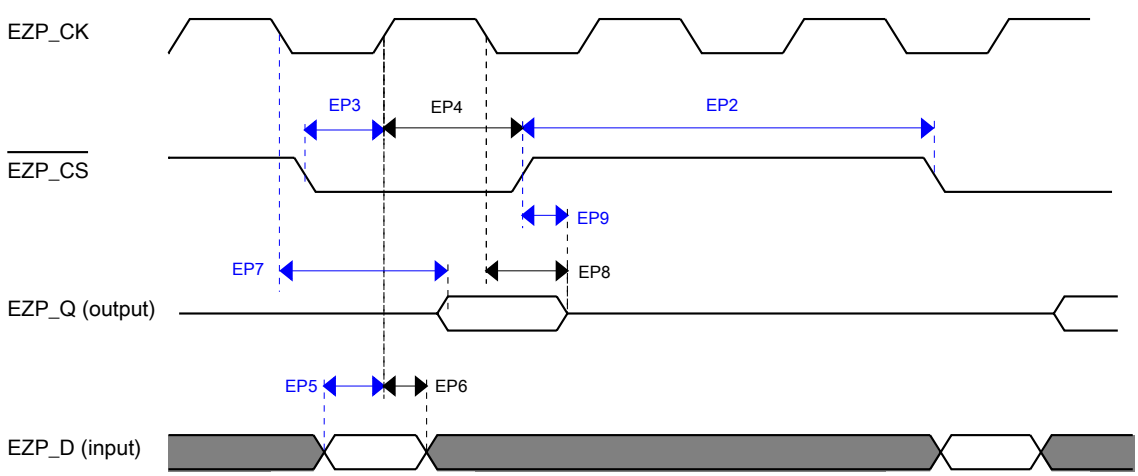

Figure 12. EzPort Timing Diagram

6.4.3 NFC specifications

The NAND flash controller (NFC) implements the interface to standard NAND flash memory devices. This section describes the timing parameters of the NFC.

In the following table:

Table 25. NFC specifications (continued)

Num	Description	Min.	Max.	Unit
t_{WP}	$\overline{\text{NFC\_WP}}$ pulse width	$T_L - 1$	—	ns
t_{ALS}	NFC_ALE setup time	$2T_H + T_L$	—	ns
t_{ALH}	NFC_ALE hold time	$T_H + T_L$	—	ns
t_{DS}	Data setup time	$T_L - 1$	—	ns
t_{DH}	Data hold time	$T_H - 1$	—	ns
t_{WC}	Write cycle time	$T_H + T_L - 1$	—	ns
t_{WH}	$\overline{\text{NFC\_WE}}$ hold time	$T_H - 1$	—	ns
t_{RR}	Ready to $\overline{\text{NFC\_RE}}$ low	$4T_H + 3T_L + 90$	—	ns
t_{RP}	$\overline{\text{NFC\_RE}}$ pulse width	$T_L + 1$	—	ns
t_{RC}	Read cycle time	$T_L + T_H - 1$	—	ns
t_{REH}	$\overline{\text{NFC\_RE}}$ high hold time	$T_H - 1$	—	ns
t_{IS}	Data input setup time	11	—	ns

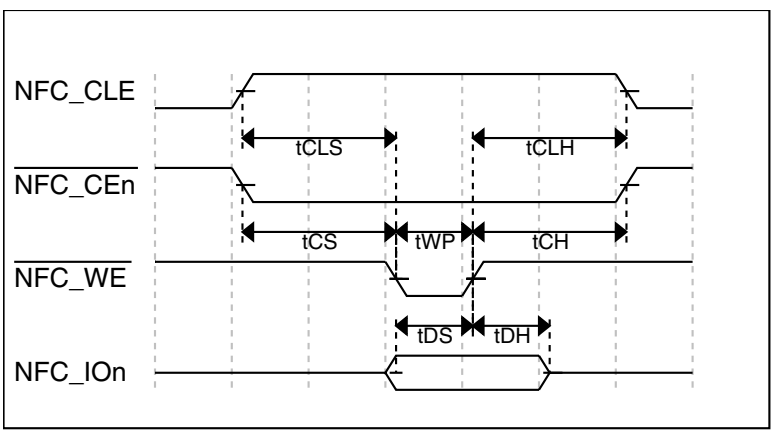

Figure 13. Command latch cycle timing

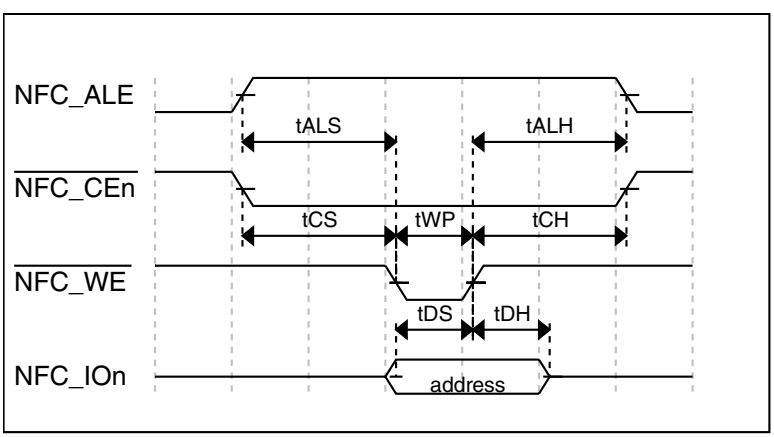

Figure 14. Address latch cycle timing

6.6 Analog

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 28 and Table 29 are achievable on the differential pins ADCx_DP0, ADCx_DM0.

The ADCx_DP2 and ADCx_DM2 ADC inputs are connected to the PGA outputs and are not direct device pins. Accuracy specifications for these pins are defined in Table 30 and Table 31.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 28. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} ($V_{DD} - V_{DDA}$)	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} ($V_{SS} - V_{SSA}$)	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	
V_{ADIN}	Input voltage	• 16-bit differential mode • All other modes	VREFL VREFL	— —	31/32 × VREFH VREFH	V	
C_{ADIN}	Input capacitance	• 16-bit mode • 8-bit / 10-bit / 12-bit modes	— —	8 4	10 5	pF	
R_{ADIN}	Input series resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance (external)	13-bit / 12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	3
f_{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	—	18.0	MHz	4
f_{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	—	12.0	MHz	4
C_{rate}	ADC conversion rate	≤ 13-bit modes					5

Table continues on the next page...

Table 28. 16-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
		No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	ksps	
C_{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37.037	—	461.467	ksps	5

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
4. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

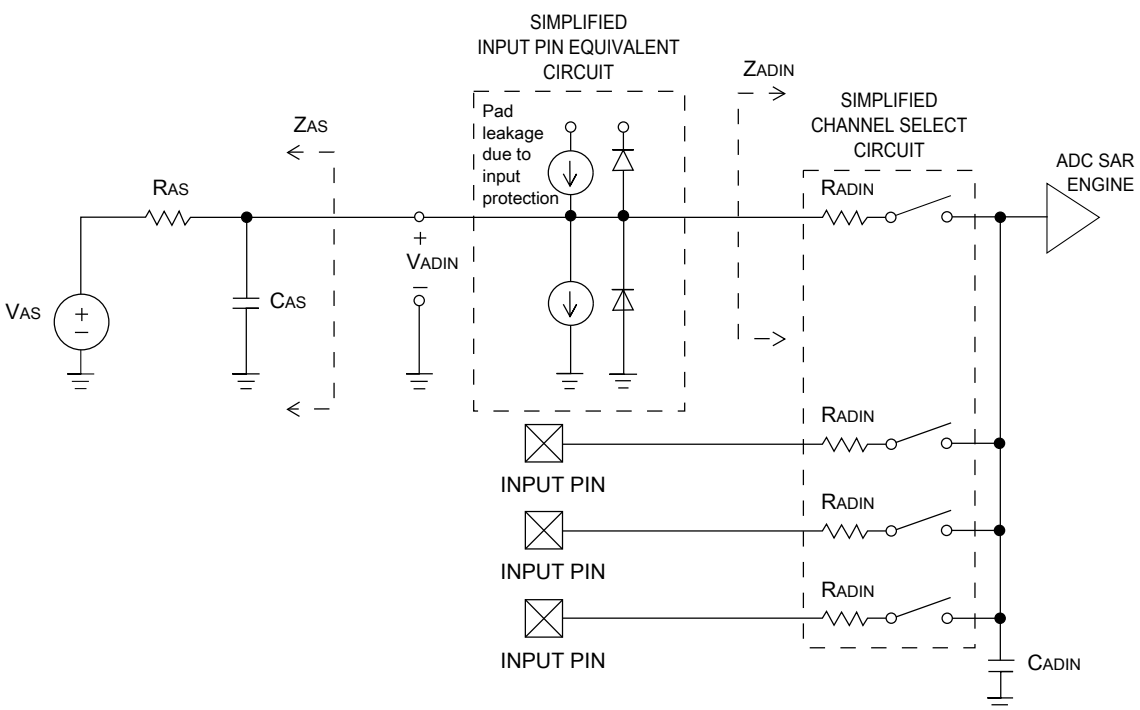

Figure 20. ADC input impedance equivalency diagram

6.6.1.2 16-bit ADC electrical characteristics

Table 29. 16-bit ADC characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
		• Avg = 32					
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

1. All accuracy numbers assume the ADC is calibrated with V_{REFH} = V_{DDA}
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
8. ADC conversion clock < 3 MHz

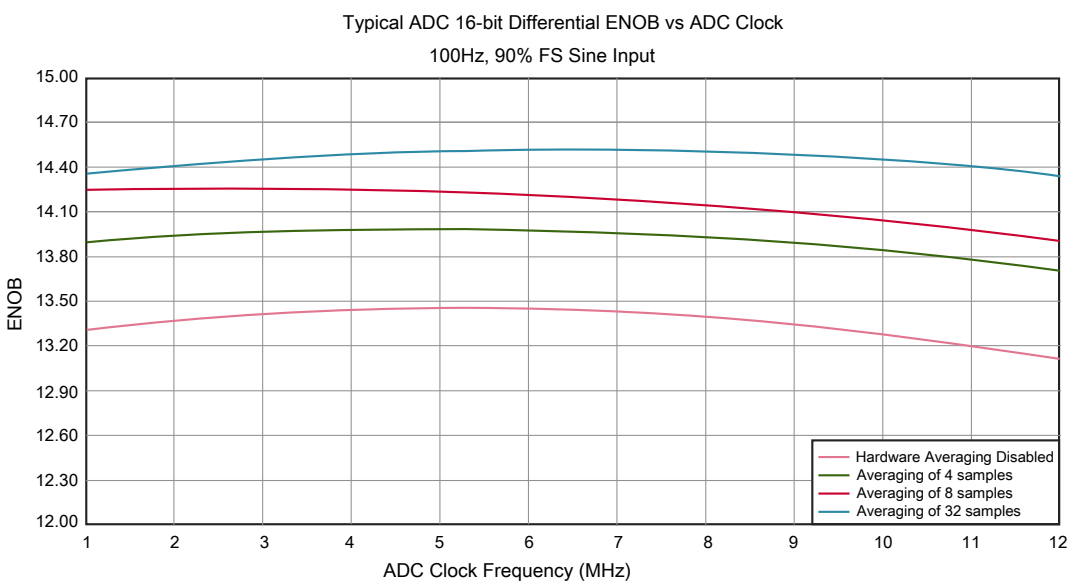

Figure 21. Typical ENOB vs. ADC_CLK for 16-bit differential mode

Table 31. 16-bit ADC with PGA characteristics (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
		• Gain=1, Average=32	11.0	14.3	—	bits	
		• Gain=2, Average=32	7.9	13.8	—	bits	
		• Gain=4, Average=32	7.3	13.1	—	bits	
		• Gain=8, Average=32	6.8	12.5	—	bits	
		• Gain=16, Average=32	6.8	11.5	—	bits	
		• Gain=32, Average=32	7.5	10.6	—	bits	
		• Gain=64, Average=32					
SINAD	Signal-to-noise plus distortion ratio	See ENOB	6.02 × ENOB + 1.76			dB	

1. Typical values assume V_{DDA} =3.0V, Temp=25°C, f_{ADCK}=6MHz unless otherwise stated.
2. This current is a PGA module adder, in addition to ADC conversion currents.
3. Between IN+ and IN-. The PGA draws a DC current from the input terminals. The magnitude of the DC current is a strong function of input common mode voltage (V_{CM}) and the PGA gain.
4. Gain = 2^{PGAG}
5. After changing the PGA gain setting, a minimum of 2 ADC+PGA conversions should be ignored.
6. Limit the input signal swing so that the PGA does not saturate during operation. Input signal swing is dependent on the PGA reference voltage and gain setting.

6.6.2 CMP and 6-bit DAC electrical specifications

Table 32. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	µA
I_{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	µA
V_{AIN}	Analog input voltage	V_{SS} – 0.3	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA

Table continues on the next page...

6.6.3.2 12-bit DAC operating behaviors

Table 34. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	150	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	700	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V_{DDA} ≥ 2.4 V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	μV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/μs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line $t_{rmax} + t_{SU; DAT}$ = 1000 + 250 = 1250 ns (according to the Standard mode I^2C bus specification) before the SCL line is released.

7. C_b = total capacitance of the one bus line in pF.

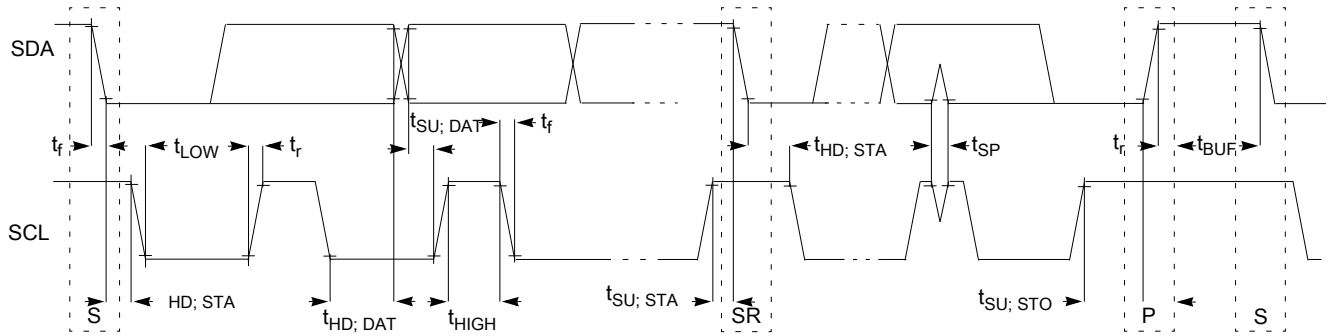

Figure 34. Timing definition for fast and standard mode devices on the I^2C bus

6.8.10 UART switching specifications

See General switching specifications.

6.8.11 SDHC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

Table 49. SDHC switching specifications over a limited operating voltage range

Num	Symbol	Description	Min.	Max.	Unit
		Operating voltage	2.7	3.6	V
		Card input clock			
SD1	fpp	Clock frequency (low speed)	0	400	kHz
	fpp	Clock frequency (SD\SDIO full speed\high speed)	0	25\50	MHz
	fpp	Clock frequency (MMC full speed\high speed)	0	20\50	MHz
	f_{OD}	Clock frequency (identification mode)	0	400	kHz
SD2	t_{WL}	Clock low time	7	—	ns
SD3	t_{WH}	Clock high time	7	—	ns
SD4	t_{TLH}	Clock rise time	—	3	ns
SD5	t_{THL}	Clock fall time	—	3	ns
		SDHC output / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)			
SD6	t_{OD}	SDHC output delay (output valid)	-5	6.5	ns
		SDHC input / card inputs SDHC_CMD, SDHC_DAT (reference to SDHC_CLK)			
SD7	t_{ISU}	SDHC input setup time	5	—	ns
SD8	t_{IH}	SDHC input hold time	0	—	ns

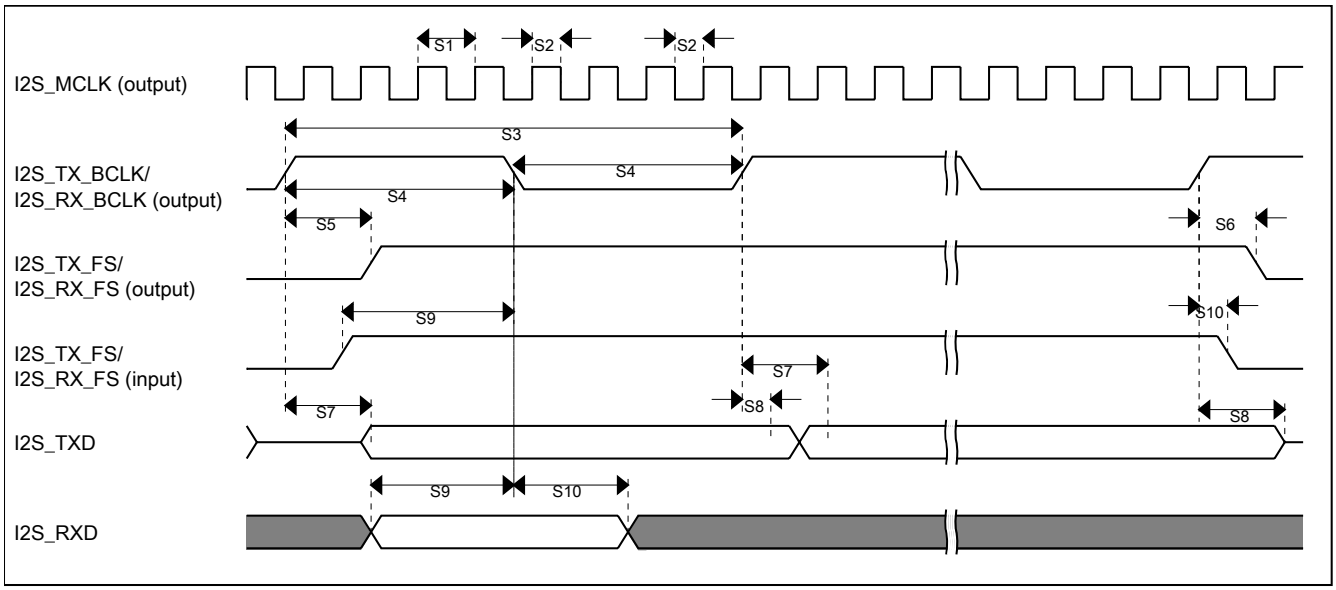

Figure 36. I2S/SAI timing — master modes

Table 52. I2S/SAI slave mode timing in Normal Run, Wait and Stop modes (limited voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	80	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	4.5	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	2	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid • Multiple SAI Synchronous mode • All other modes	 — —	 21 15	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	4.5	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	25	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

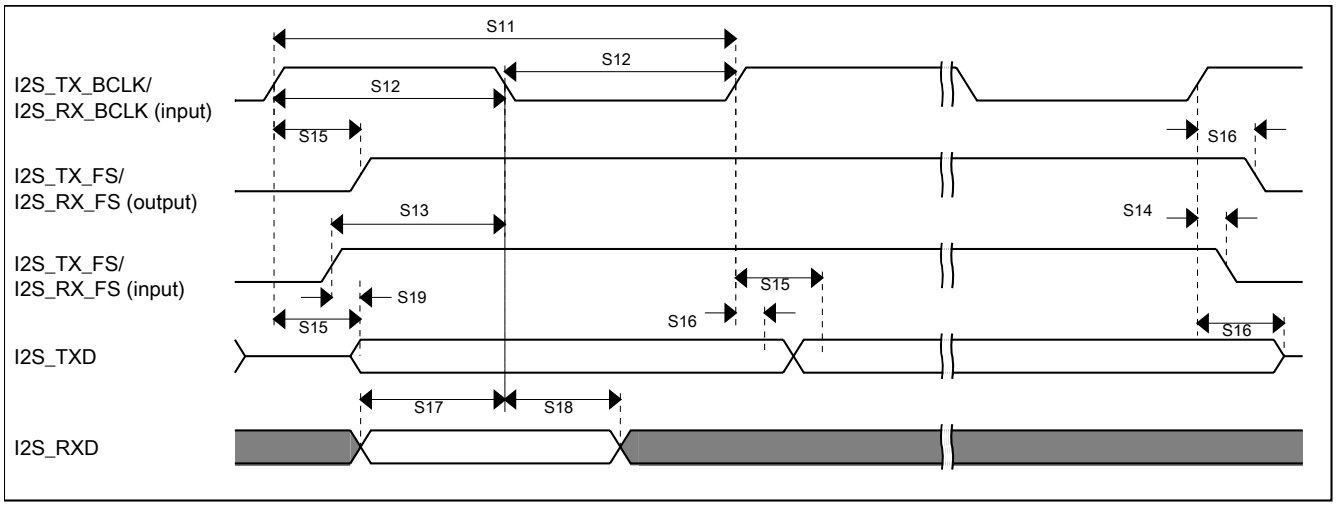

Figure 39. I2S/SAI timing — slave modes

6.8.12.3 VLPR, VLPW, and VLPS mode performance over the full operating voltage range

This section provides the operating performance over the full operating voltage for the device in VLPR, VLPW, and VLPS modes.

Table 55. I2S/SAI master mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	I2S_MCLK cycle time	62.5	—	ns
S2	I2S_MCLK pulse width high/low	45%	55%	MCLK period
S3	I2S_TX_BCLK/I2S_RX_BCLK cycle time (output)	250	—	ns
S4	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low	45%	55%	BCLK period
S5	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output valid	—	45	ns
S6	I2S_TX_BCLK/I2S_RX_BCLK to I2S_TX_FS/ I2S_RX_FS output invalid	0	—	ns
S7	I2S_TX_BCLK to I2S_TXD valid	—	45	ns
S8	I2S_TX_BCLK to I2S_TXD invalid	-1.6	—	ns
S9	I2S_RXD/I2S_RX_FS input setup before I2S_RX_BCLK	45	—	ns
S10	I2S_RXD/I2S_RX_FS input hold after I2S_RX_BCLK	0	—	ns

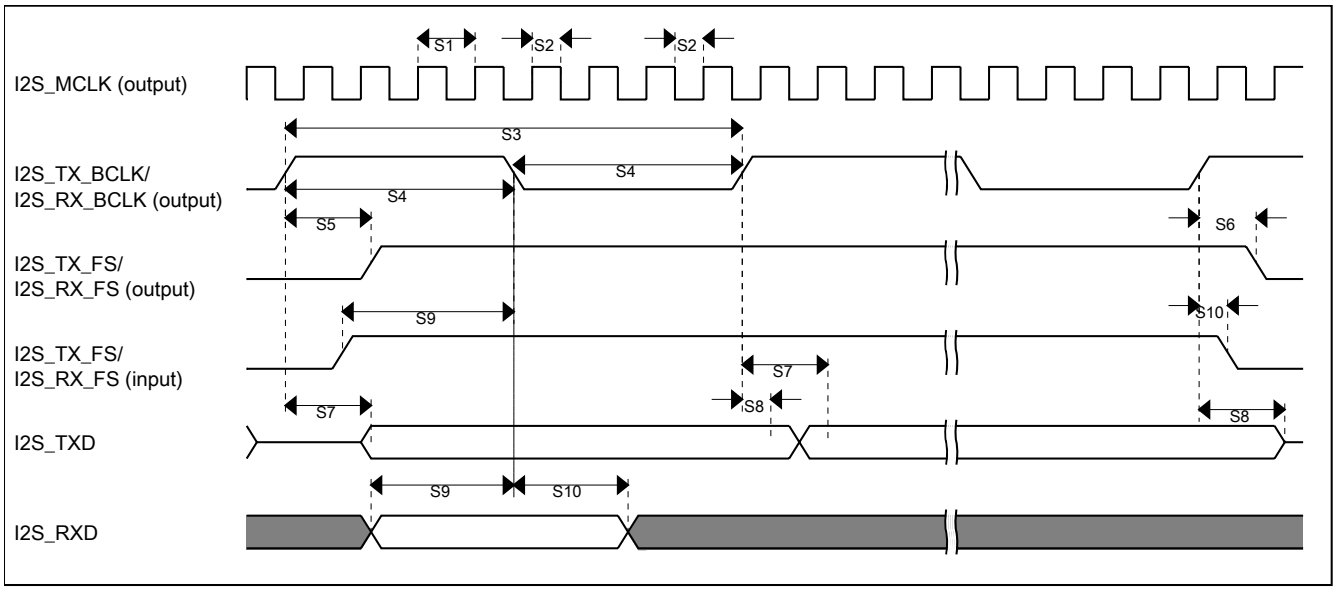

Figure 40. I2S/SAI timing — master modes

Table 56. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range)

Num.	Characteristic	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S11	I2S_TX_BCLK/I2S_RX_BCLK cycle time (input)	250	—	ns
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	3	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	63	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid[1]	—	72	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

144 MAP BGA	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
L3	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23								
L4	DAC1_OUT/ CMP0_IN4/ CMP2_IN3/ ADC1_SE23	DAC1_OUT/ CMP0_IN4/ CMP2_IN3/ ADC1_SE23	DAC1_OUT/ CMP0_IN4/ CMP2_IN3/ ADC1_SE23								
L5	TAMPER0/ RTC_ WAKEUP_B	TAMPER0/ RTC_ WAKEUP_B	TAMPER0/ RTC_ WAKEUP_B								
K5	TAMPER1	TAMPER1	TAMPER1								
K4	TAMPER2	TAMPER2	TAMPER2								
J4	TAMPER3	TAMPER3	TAMPER3								
H4	TAMPER4	TAMPER4	TAMPER4								
M4	TAMPER5	TAMPER5	TAMPER5								
M7	XTAL32	XTAL32	XTAL32								
M6	EXTAL32	EXTAL32	EXTAL32								
L6	VBAT	VBAT	VBAT								
J5	PTA0	JTAG_TCLK/ SWD_CLK/ EZP_CLK	TSI0_CH1	PTA0	UART0_CTS_ b/ UART0_COL_ b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
J6	PTA1	JTAG_TDI/ EZP_DI	TSI0_CH2	PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
K6	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSI0_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
K7	PTA3	JTAG_TMS/ SWD_DIO	TSI0_CH4	PTA3	UART0_RTS_ b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
L7	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSI0_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b
M8	PTA5	DISABLED		PTA5	USB_CLKIN	FTM0_CH2	RMII0_RXER/ MII0_RXER	CMP2_OUT	I2S0_TX_ BCLK	JTAG_TRST_ b	
E7	VDD	VDD	VDD								
G7	VSS	VSS	VSS								
J7	PTA6	ADC3_SE6a	ADC3_SE6a	PTA6	ULPI_CLK	FTM0_CH3	I2S1_RXD0			TRACE_ CLKOUT	
J8	PTA7	ADC0_SE10	ADC0_SE10	PTA7	ULPI_DIR	FTM0_CH4	I2S1_RX_ BCLK			TRACE_D3	
K8	PTA8	ADC0_SE11	ADC0_SE11	PTA8	ULPI_NXT	FTM1_CH0	I2S1_RX_FS		FTM1_QD_ PHA	TRACE_D2	
L8	PTA9	ADC3_SE5a	ADC3_SE5a	PTA9	ULPI_STP	FTM1_CH1	MII0_RXD3		FTM1_QD_ PHB	TRACE_D1	
M9	PTA10	ADC3_SE4a	ADC3_SE4a	PTA10	ULPI_DATA0	FTM2_CH0	MII0_RXD2		FTM2_QD_ PHA	TRACE_D0	
L9	PTA11	ADC3_SE15	ADC3_SE15	PTA11	ULPI_DATA1	FTM2_CH1	MII0_RXCLK		FTM2_QD_ PHB		